Pb Free Plating Product

GTM CORPORATION

ISSUED DATE :2004/10/12
REVISED DATE :2005/03/22B

G2304

N-CHANNEL ENHANCEMENT MODE POWER MOSFET

BV_{DSS}	25V
$R_{DS(ON)}$	117mΩ
I_D	2.7A

Description

The G2304 provides the designer with the best combination of fast switching, low on-resistance and cost-effectiveness.

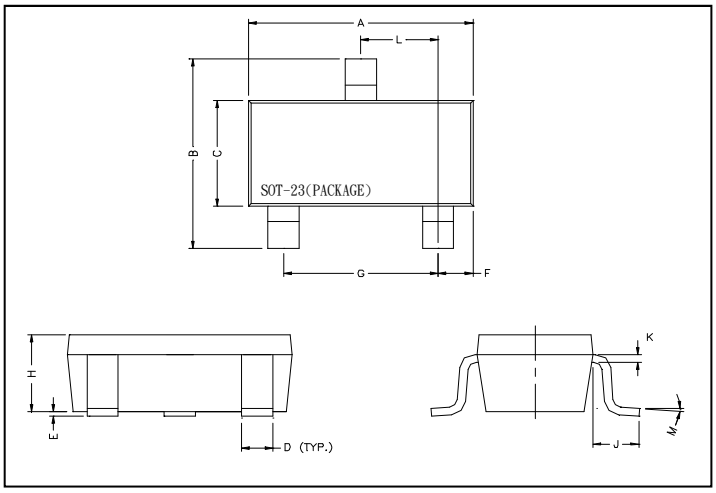
Features

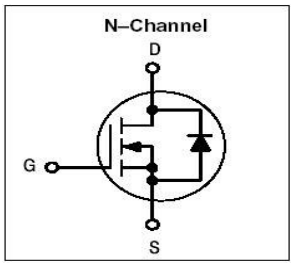
- Super High Dense Cell Design for Extremely Low $R_{DS(ON)}$
- Reliable and Rugged

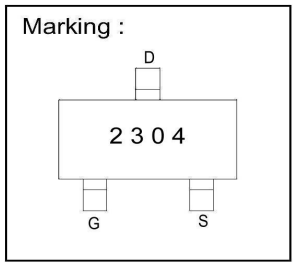
Applications

- Power Management in Notebook Computer
- Portable Equipment
- Battery Powered System.

Package Dimensions







REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	2.70	3.10	G	1.90	REF.
B	2.40	2.80	H	1.00	1.30
C	1.40	1.60	K	0.10	0.20
D	0.35	0.50	J	0.40	-
E	0	0.10	L	0.85	1.15
F	0.45	0.55	M	0°	10°

Absolute Maximum Ratings

Parameter	Symbol	Ratings	Unit
Drain-Source Voltage	V_{DS}	25	V
Gate-Source Voltage	V_{GS}	±20	V
Continuous Drain Current[3], V_{GS}@4.5V	I_D @T_A=25℃	2.7	A
Continuous Drain Current[3], V_{GS}@4.5V	I_D @T_A=70℃	2.2	A
Pulsed Drain Current[1,2]	I_{DM}	10	A
Power Dissipation	P_D @T_A=25℃	1.38	W
Linear Derating Factor		0.01	W/℃
Operating Junction and Storage Temperature Range	Tj, Tstg	-55 ~ +150	℃

Thermal Data

Parameter	Symbol	Ratings	Unit
Thermal Resistance Junction-ambient[3] Max.	Rthj-a	90	℃/W

Electrical Characteristics(Tj = 25℃ Unless otherwise specified)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Drain-Source Breakdown Voltage	BV_{DSS}	25	-	-	V	V_{GS}=0, I_D=250uA
Breakdown Voltage Temperature Coefficient	$\triangle BV_{DSS}/\triangle Tj$	-	0.1	-	V/℃	Reference to 25℃, I_D=1mA
Gate Threshold Voltage	$V_{GS(th)}$	1.0	-	3.0	V	V_{DS}= V_{GS}, I_D=250uA
Forward Transconductance	gfs	-	3.4	-	S	V_{DS}=4.5V, I_D=2.5A
Gate-Source Leakage Current	I_{GSS}	-	-	±100	nA	V_{GS}= ±20V
Drain-Source Leakage Current(Tj=25℃)	I_{DSS}	-	-	1	uA	V_{DS}=25V, V_{GS}=0
Drain-Source Leakage Current(Tj=70℃)		-	-	10	uA	V_{DS}=25V, V_{GS}=0
Static Drain-Source On-Resistance[2]	$R_{DS(ON)}$	-	-	117	mΩ	I_D=2.5A, V_{GS}=10V
		-	-	190		I_D=2.0A, V_{GS}=4.5V
Total Gate Charge[2]	Q_g	-	5.9	10	nC	I_D=2.5A
Gate-Source Charge	Q_{gs}	-	0.8	-		V_{DS}=15V
Gate-Drain ("Miller") Change	Q_{gd}	-	2.1	-		V_{GS}=10V
Turn-on Delay Time[2]	$T_{d(on)}$	-	4.5	-	ns	V_{DS}=15V I_D=1A V_{GS}=10V R_G=6Ω R_D=15Ω
Rise Time	T_r	-	11.5	-		
Turn-off Delay Time	$T_{d(off)}$	-	12	-		
Fall Time	T_f	-	3	-		
Input Capacitance	C_{iss}	-	110	-	pF	V_{GS}=0V V_{DS}=15V f=1.0MHz
Output Capacitance	C_{oss}	-	85	-		
Reverse Transfer Capacitance	C_{rss}	-	39	-		

Source-Drain Diode

Forward On Voltage[2]	V_{SD}	-	-	1.2	V	I_S=1.25A, V_{GS}=0 Tj=25℃
Continuous Source Current(Body Diode)	Is	-	-	1	A	V_D= V_G=0V, V_S=1.2V
Pulsed Source Current (Body Diode)[1]	Ism	-	-	10	A	

Notes: 1. Pulse width limited by Max. junction temperature.
2. Pulse width≦300us, duty cycle≦2%.
3. Surface mounted on 1 in^2 copper pad of FR4 board;270℃/w when mounted on min. copper pad.

Characteristics Curve

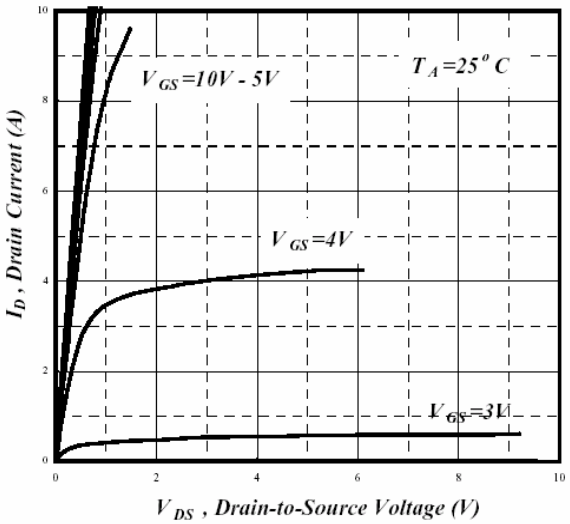


Fig 1. Typical Output Characteristics

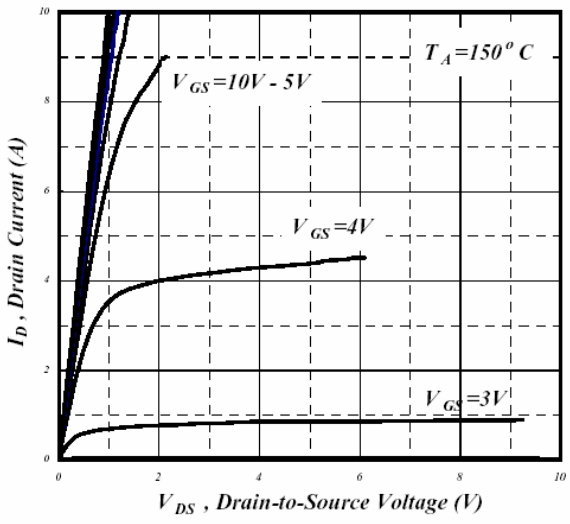


Fig 2. Typical Output Characteristics

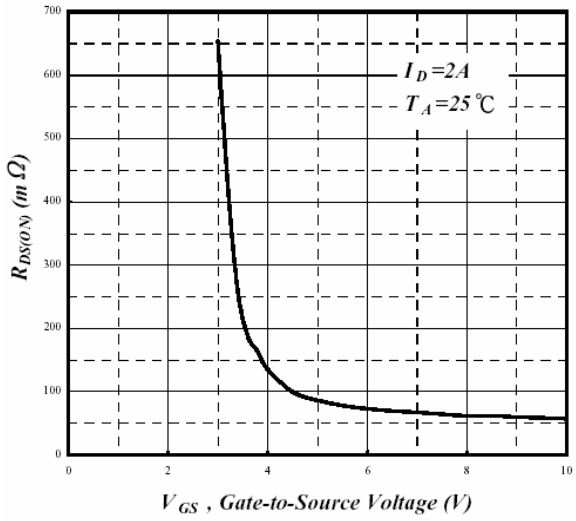


Fig 3. On-Resistance v.s. Gate Voltage

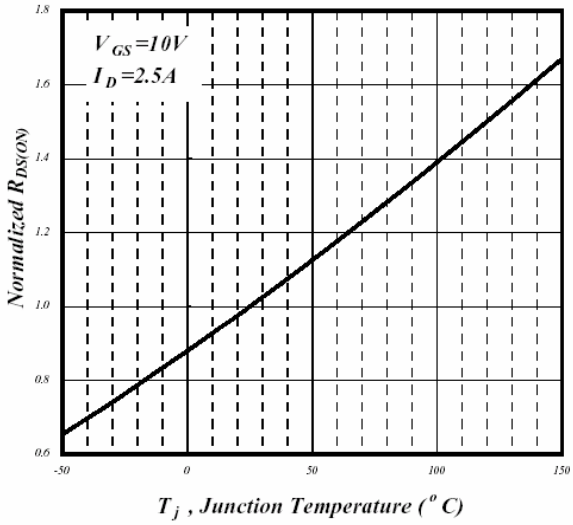


Fig 4. Normalized On-Resistance v.s. Junction Temperature

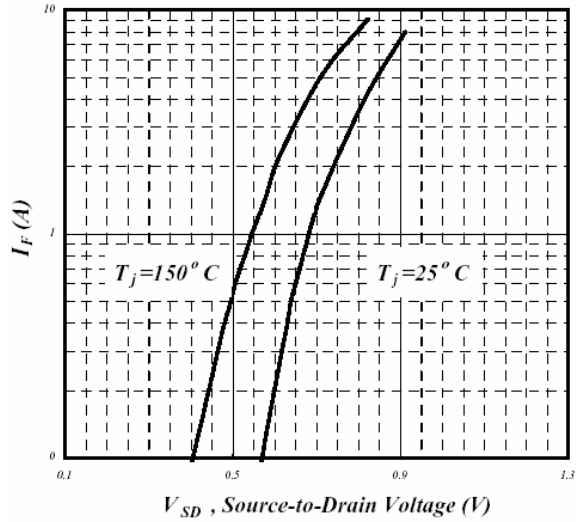


Fig 5. Forward Characteristic of Reverse Diode

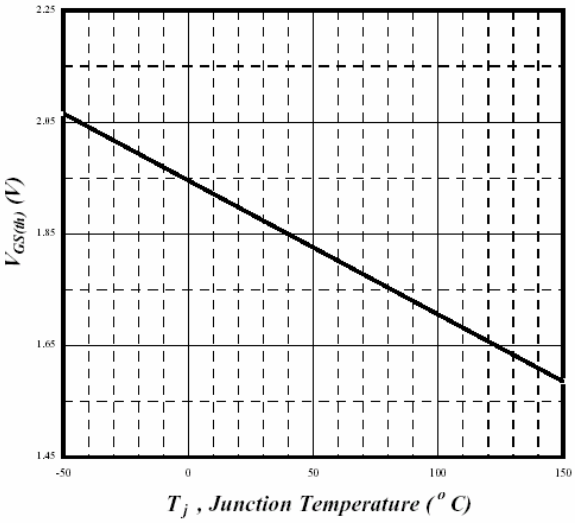


Fig 6. Gate Threshold Voltage v.s. Junction Temperature

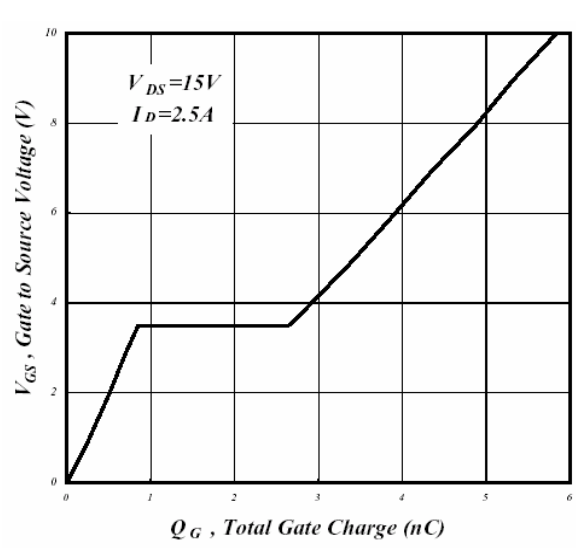


Fig7. Gate Charge Characteristics

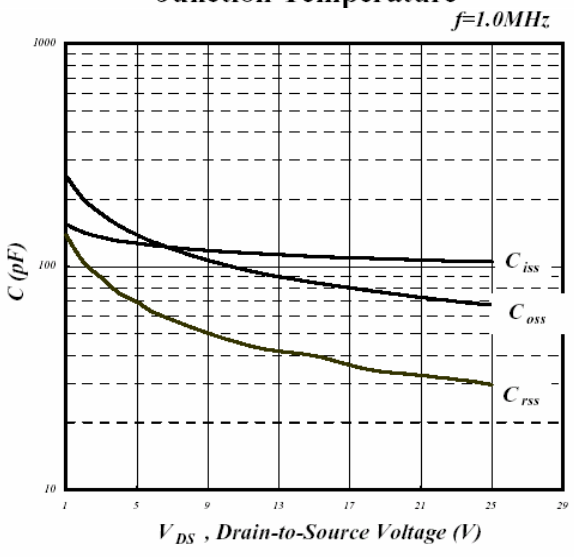


Fig 8. Typical Capacitance Characteristics

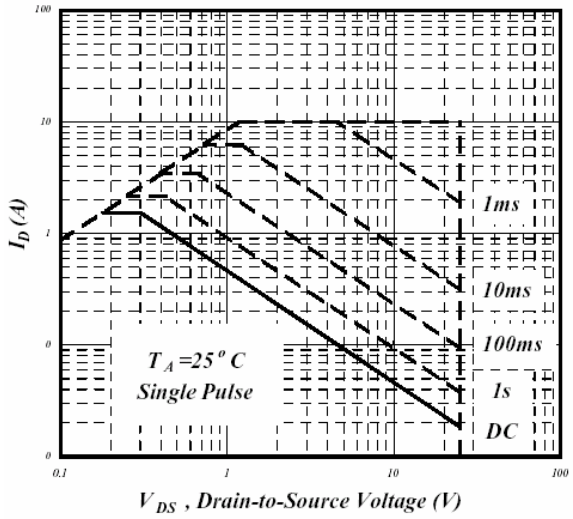


Fig 9. Maximum Safe Operating Area

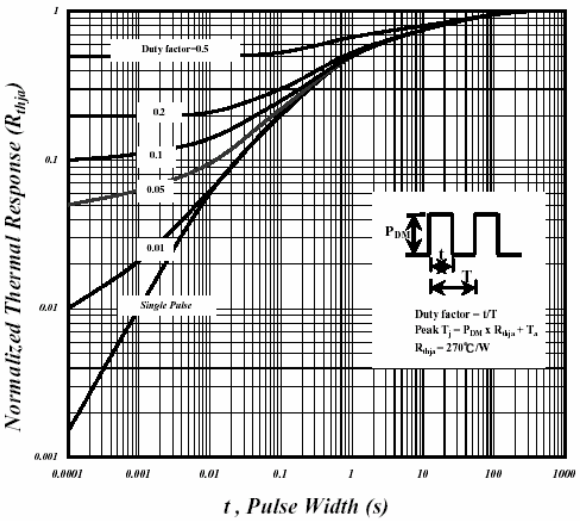


Fig10. Effective Transient Thermal Impedance

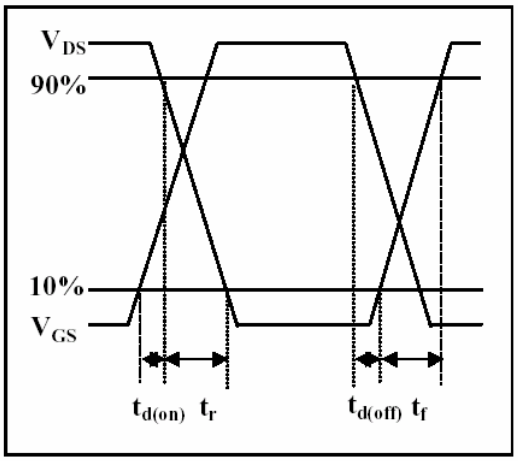


Fig 11. Switching Time Waveform

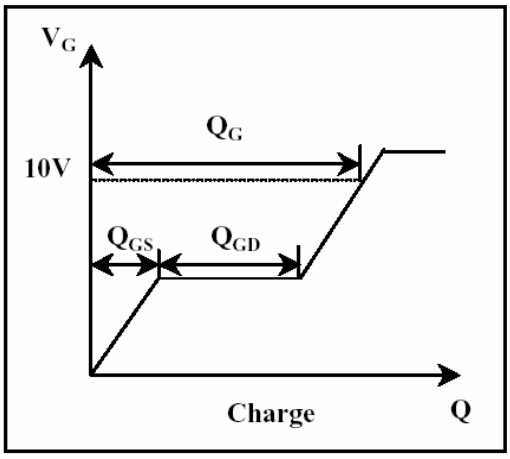


Fig 12. Gate Charge Waveform

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